NVMFS5832NL

Power MOSFET

40 V, 4.2 mΩ, 120 A, Single N−Channel

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- AEC−Q101 Qualified and PPAP Capable
- These are Pb−Free Devices

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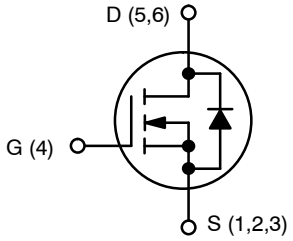
$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
40 V	4.2 mΩ @ 10 V	120 A
	6.5 mΩ @ 4.5 V	



N−CHANNEL MOSFET

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

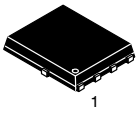
Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	40	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current $R_{\Psi J-mb}$ (Notes 1, 2, 3, 4)	Steady State	T_{mb} = 25°C	I_D	120	A
		T_{mb} = 100°C		84	
Power Dissipation $R_{\Psi J-mb}$ (Notes 1, 2, 3)		T_{mb} = 25°C	P_D	127	W
		T_{mb} = 100°C		64	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 3, 4)	Steady State	T_A = 25°C	I_D	21	A
		T_A = 100°C		15	
Power Dissipation $R_{\theta JA}$ (Notes 1 & 3)		T_A = 25°C	P_D	3.7	W
		T_A = 100°C		1.9	
Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		I_{DM}	557	A
Operating Junction and Storage Temperature			T_J, T_{stg}	−55 to +175	°C
Source Current (Body Diode)			I_S	120	A
Single Pulse Drain−to−Source Avalanche Energy (T_J = 25°C, V_{GS} = 10 V, $I_{L(pk)}$ = 52 A, L = 0.1 mH, R_G = 25 Ω)			E_{AS}	134	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE MAXIMUM RATINGS

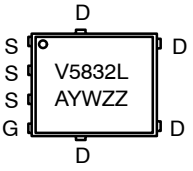
Parameter	Symbol	Value	Unit
Junction−to−Mounting Board (top) − Steady State (Notes 2, 3)	$R_{\Psi J-mb}$	1.2	°C/W
Junction−to−Ambient − Steady State (Note 3)	$R_{\theta JA}$	40	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Psi (Ψ) is used as required per JESD51−12 for packages in which substantially less than 100% of the heat flows to single case surface.
3. Surface−mounted on FR4 board using a 650 mm^2, 2 oz. Cu pad.
4. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



SO−8 FLAT LEAD CASE 488AA STYLE 1

MARKING DIAGRAM



A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
NVMFS5832NLT1G	SO−8FL (Pb−Free)	1500 / Tape & Reel
NVMFS5832NLT3G	SO−8FL (Pb−Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		40			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				34.2		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 40 V	T_J = 25 °C			1	μA
			T_J = 125°C			100	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		1.4		2.4	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				6.4		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 20 A		3.1	4.2	mΩ
		V_{GS} = 4.5 V	I_D = 20 A		5.0	6.5	
Forward Transconductance	g_{FS}	V_{DS} = 15 V, I_D = 20 A			21		S
CHARGES, CAPACITANCES & GATE RESISTANCE							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = 25 V			2700		pF
Output Capacitance	C_{OSS}				360		
Reverse Transfer Capacitance	C_{RSS}				250		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 20 V; I_D = 20 A			25		nC
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 20 V; I_D = 20 A			51		
Threshold Gate Charge	$Q_{G(TH)}$	V_{GS} = 4.5 V, V_{DS} = 20 V; I_D = 20 A			2.0		
Gate−to−Source Charge	Q_{GS}				8.0		
Gate−to−Drain Charge	Q_{GD}				12.7		
Plateau Voltage	V_{GP}				3.2		V
SWITCHING CHARACTERISTICS (Note 6)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 4.5 V, V_{DS} = 20 V, I_D = 10 A, R_G = 1.0 Ω			13		ns
Rise Time	t_r				24		
Turn−Off Delay Time	$t_{d(OFF)}$				27		
Fall Time	t_f				8.0		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 5 A	T_J = 25°C		0.73	1.2	V
			T_J = 125°C		0.57		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dIS/dt = 100 A/μs, I_S = 10 A			28.6		ns
Charge Time	t_a				14		
Discharge Time	t_b				14.5		
Reverse Recovery Charge	Q_{RR}				23.4		nC

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

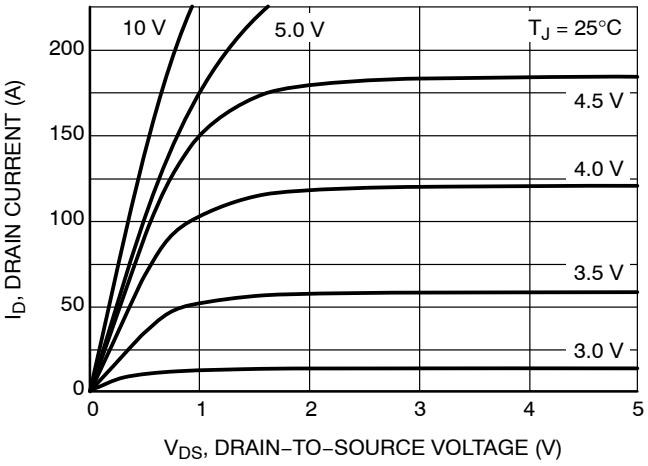


Figure 1. On−Region Characteristics

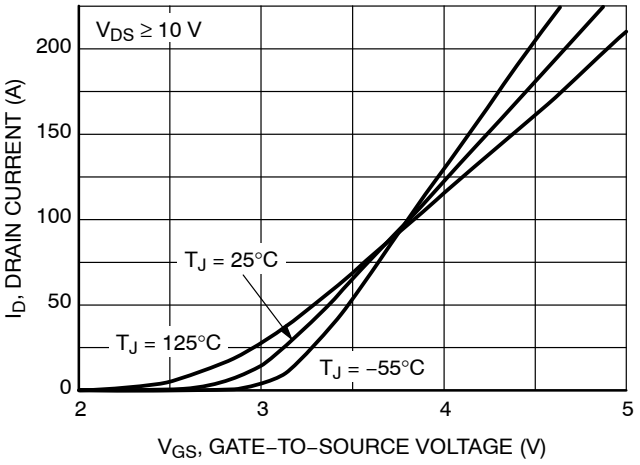


Figure 2. Transfer Characteristics

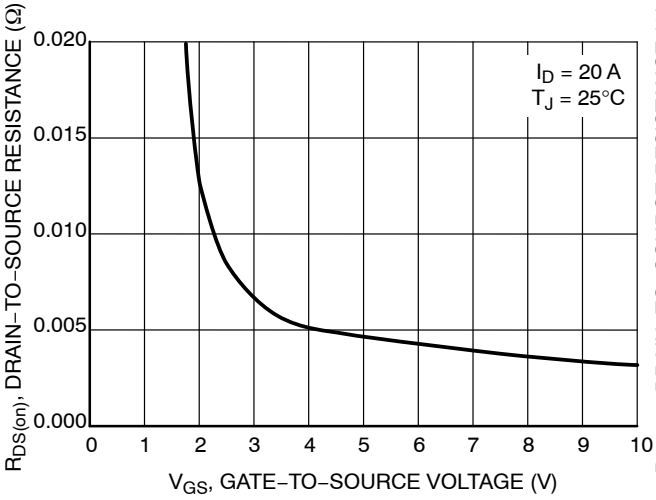


Figure 3. On−Resistance vs. Gate−to−Source Voltage

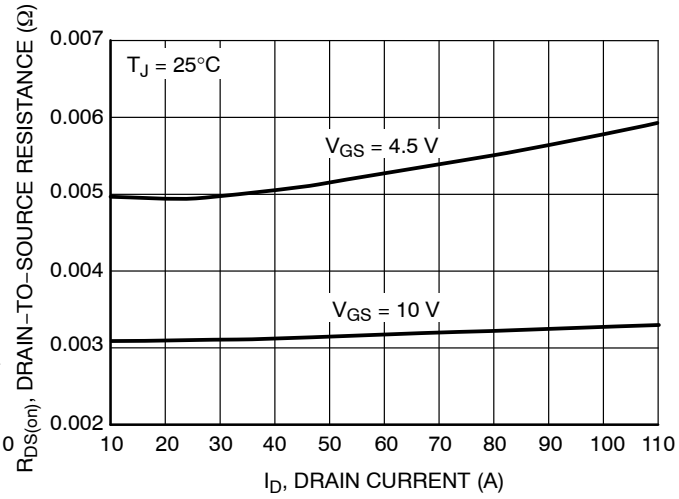


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

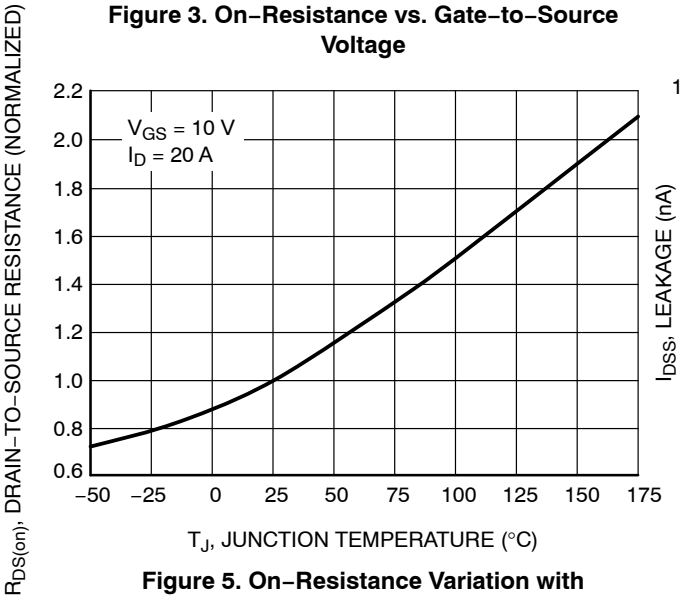


Figure 5. On−Resistance Variation with Temperature

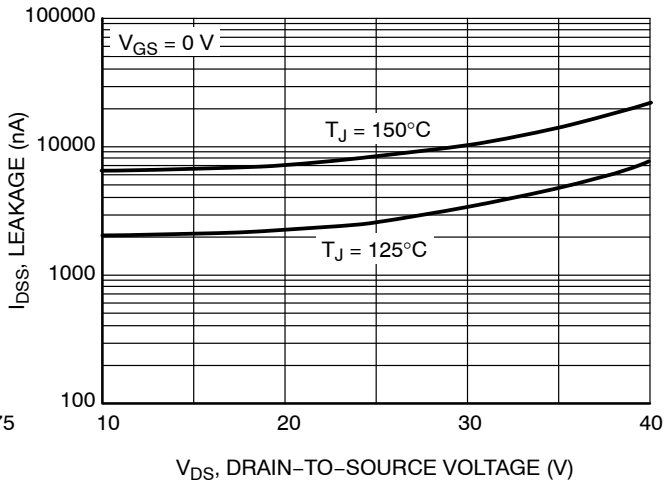


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

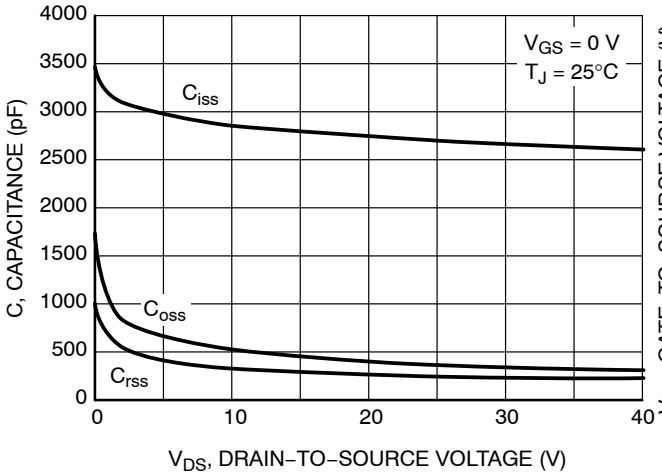


Figure 7. Capacitance Variation

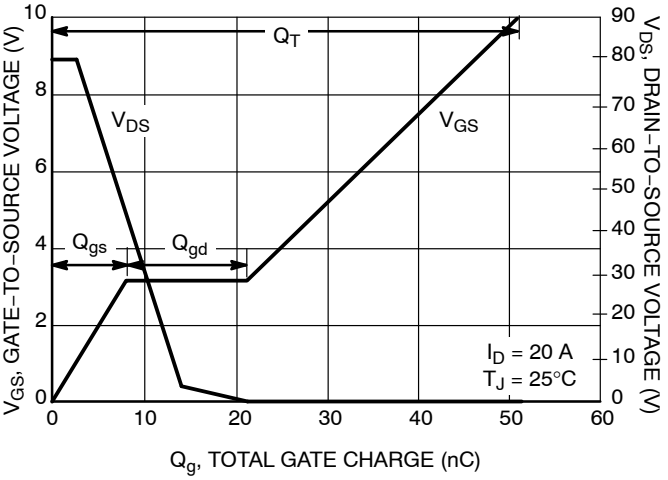


Figure 8. Gate−to−Source Voltage vs. Total Charge

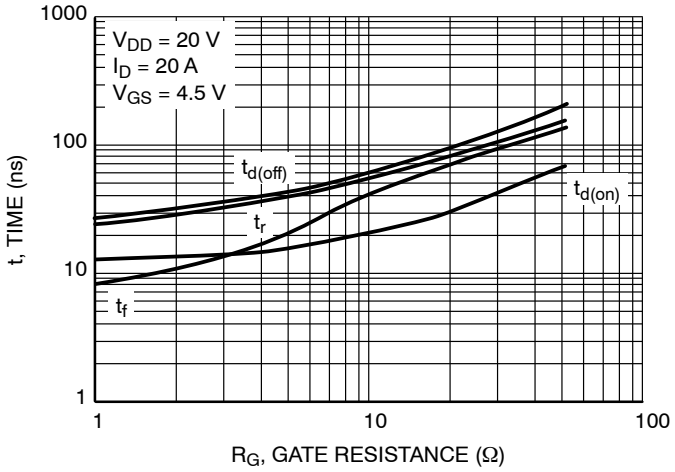


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

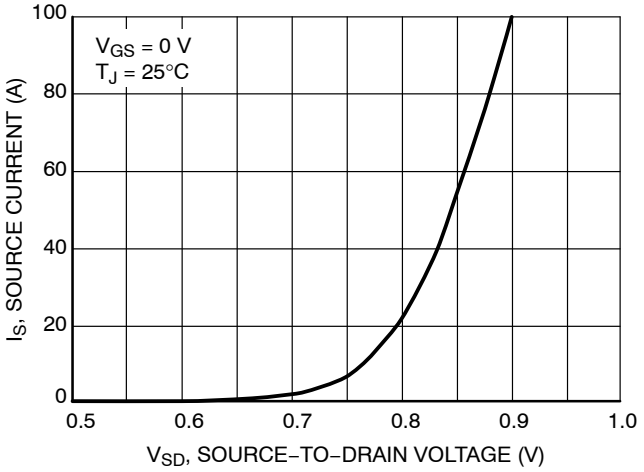


Figure 10. Diode Forward Voltage vs. Current

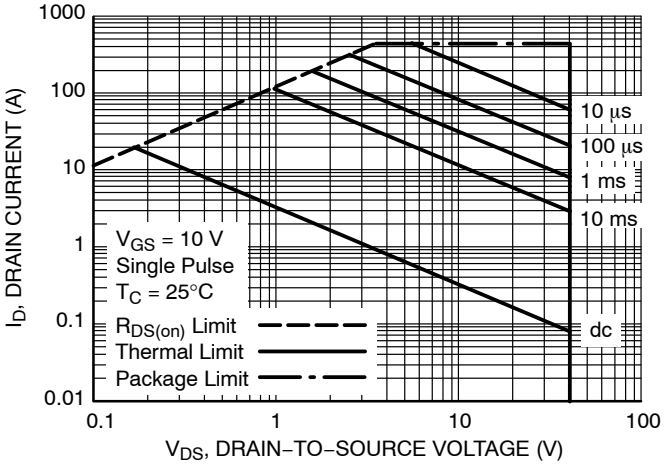


Figure 11. Maximum Rated Forward Biased Safe Operating Area

TYPICAL CHARACTERISTICS

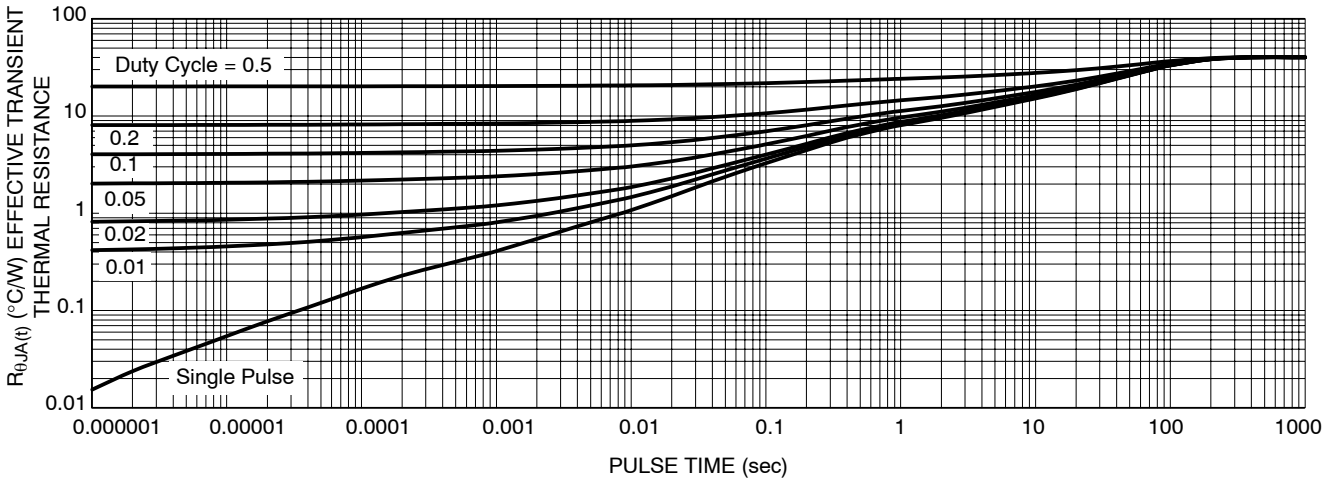
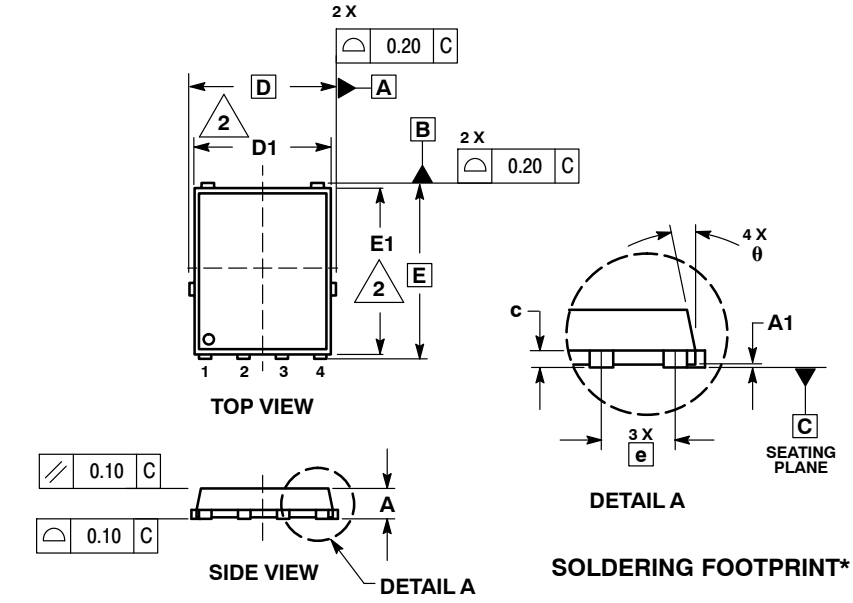


Figure 12. Thermal Response

PACKAGE DIMENSIONS

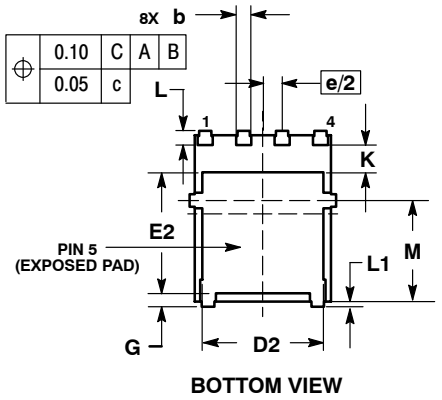
DFN5 5x6, 1.27P
(SO−8FL)
CASE 488AA
ISSUE H



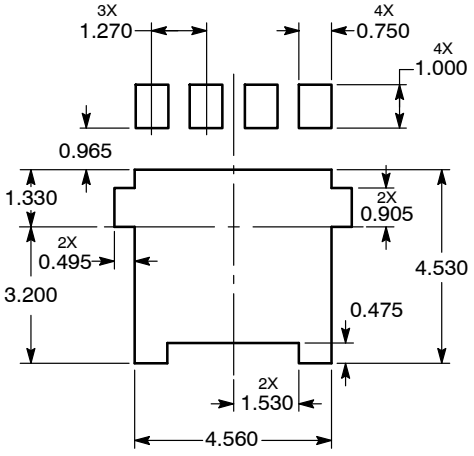
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D		5.15 BSC	
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E		6.15 BSC	
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e		1.27 BSC	
G	0.51	0.61	0.71
K	1.20	1.35	1.50
L	0.51	0.61	0.71
L1	0.05	0.17	0.20
M	3.00	3.40	3.80
θ	0 °	---	12 °

STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN



SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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